SBD120D1 Schottky Barrier Diode 200V Maximum Repetitive Peak Reverse Voltage Electronic Component Diode

Our Product Introduction

Basic Information

- Place of Origin: Shenzhen,China
- Brand Name: Socay
- Certification: REACH,RoHS,ISO
- Model Number: SBD120D1
- Minimum Order Quantity: 3000PCS/REEL
- Packaging Details: per 7" plastic Reel

Product Specification

- Maximum Forward Voltage At IF=1A: 0.85V
- Operating Junction Temperature And Storage Temperature Range: -55 To +150
- Maximum Repetitive Peak Reverse Voltage: 200V
- Reverse Leakage Current At VRRM: 30μA
- Typical Junction Capacitance Rating At VR=0V: 85pF
- Average Rectified Current: 1A

Product Description

Product Description:

With an operating junction temperature range of -55 to +150 and a storage temperature range of -55 to +150 , this diode is highly reliable and can withstand extreme temperatures without losing its functionality. It has a maximum repetitive peak reverse voltage of 200V, making it suitable for use in various circuit designs.
Our Schottky Barrier Diode has a reverse leakage current of 30µA at VRRM, which ensures optimal performance and efficiency. It also has an average rectified current of 1A, making it an ideal choice for high forward surge current applications. This diode is perfect for use in various electronic applications, including power supplies, voltage regulators, and DC-DC converters.
Additionally, this diode has a typical junction capacitance rating of 85pF at VR=0V, making it an excellent choice for use in circuits that require high-speed switching and low noise. It is a versatile and reliable semiconductor device that can be used in a wide range of electronic applications.
Our Schottky Barrier Diode is a semiconductor device that is an essential component in various circuit designs. It is highly reliable and can withstand extreme temperatures without losing its functionality. This diode has a maximum repetitive peak reverse voltage of 200V, a reverse leakage current of 30µA at VRRM, and an average rectified current of 1A, making it ideal for high forward surge current applications. Additionally, it has a typical junction capacitance rating of 85pF at VR=0V, making it an excellent choice for use in circuits that require high-speed switching and low noise.

Features:

Product Name: Schottky Barrier Diode
Operating Junction Temperature and Storage Temperature Range: -55 To +150
Reverse Leakage Current at VRRM: 30µA
Maximum Repetitive Peak Reverse Voltage: 200V
Maximum Forward Voltage at IF=1A: 0.85V
Typical Junction Capacitance Rating at VR=0V: 85pF
Product Type: Electrostatic Diode
Product Category: Surface Mount Schottky Barrier Rectifiers
Related Products: Diode Triode Transistor

Technical Parameters:

Product Attribute	Value
Maximum Forward Voltage at IF=1A	0.85V
Typical Junction Capacitance Rating at VR=0V	85pF
Average Rectified Current	1A
Reverse Leakage Current at VRRM	30µA
Operating Junction Temperature and Storage Temperature Range	-55 To +150
Maximum Repetitive Peak Reverse Voltage	200V
Maximum RMS Voltage	140V
Maximum DC Blocking Voltage	200V

This table displays technical parameters for a Surface mounted Schottky Barrier Rectifier. It has a Maximum Forward Voltage at IF=1A of 0.85V, a Typical Junction Capacitance Rating at VR=0V of 85pF, an Average Rectified Current of 1A, a Reverse Leakage Current at VRRM of 30µA, Operating Junction Temperature and Storage Temperature Range of -55 To +150 , a Maximum Repetitive Peak Reverse Voltage of 200V, a Maximum RMS Voltage of 140V, and a Maximum DC Blocking Voltage of 200V.

Applications:

The SBD120D1 Schottky Barrier Diode is a bridge rectifier diode that is designed to handle an average rectified current of 1A. It has a typical junction capacitance rating of 85pF at VR=0V, which makes it suitable for applications that require fast switching speeds. This diode electronic component can operate within a wide temperature range of -55 to +150 , making it ideal for use in harsh environments.
The maximum repetitive peak reverse voltage for the SBD120D1 Schottky Barrier Diode is 200V, and it has a reverse leakage current of 30µA at VRRM. This makes it a reliable choice for applications that require high voltage rectification and low leakage current.
The SBD120D1 Schottky Barrier Diode is commonly used in various applications, including power supplies, battery chargers, voltage regulators, and DC-DC converters. It is also suitable for use in audio amplifiers, RF detectors, and mixers.
Overall, the SBD120D1 Schottky Barrier Diode is a high-quality electronic component diode that offers reliable performance and a wide range of applications. Its certifications and cost-effective manufacturing make it an ideal choice for manufacturers looking for a reliable and cost-effective diode electronic component.

Customization:

- Place of Origin: Shenzhen, China
- Certification: REACH, RoHS, ISO
- Minimum Order Quantity: 3000PCS/REEL
- Packaging Details: per 7" plastic Reel
- Maximum Repetitive Peak Reverse Voltage: 200V

- Maximum RMS Voltage: 140V
- Operating Junction Temperature and Storage Temperature Range: -55 To +150
- Typical Junction Capacitance Rating at VR=0V: 85pF
- Reverse Leakage Current at VRRM: 30μA

This product is a High forward surge current Semiconductor and Electrostatic Diode.

FAQ:

Q: What is the brand name of this Schottky Barrier Diode product?
A: The brand name of this product is Socay.
Q: What is the model number of this Socay Schottky Barrier Diode?
A: The model number of this product is SBD120D1.
Q: Where is this Socay Schottky Barrier Diode manufactured?
A: This product is manufactured in Shenzhen, China.
Q: What certifications does this Socay Schottky Barrier Diode have?
A: This product has the following certifications: REACH, RoHS, and ISO.
Q: What is the minimum order quantity for this Socay Schottky Barrier Diode?
A: The minimum order quantity for this product is 3000PCS/REEL.
Q: How is this Socay Schottky Barrier Diode packaged?
A: This product is packaged per 7" plastic Reel.

Shenzhen Socay Electronics Co., Ltd.

+8618126201429 sylvia@socay.com socaydiode.com

4/F, Block C, HeHengXing Science & Technology Park, 19 MinQing Road, LongHua District, Shenzhen City, GuangDong Province, China